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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>			<b>Application Number</b>	10/582,392
			<b>Filing Date</b>	June 28, 2007
			<b>First Named Inventor</b>	Horsky et al.
			<b>Group Art Unit</b>	2821
			<b>Examiner Name</b>	Bernard Souw
(use as many sheets as necessary)			<b>Attorney Docket Number</b>	211843-00044
<b>Sheet</b>	1	of	1	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
/B.S./	A1	5,497,006	03-05-1996	Sferlazzo	
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	A3	2004-0002202	01-01-2004	Horsky	
	A4	2008-0223409	04-18-2008	Horsky	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>2</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
/B.S./	B1	WO 2005/059942 A2				
/B.S./	B2	WO 2004/003973 A3				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published				T <sup>2</sup>
/B.S./	C1	E.J. Colliart et al. "Co-Implantation with Conventional Spike Anneal Solutions for 45 nm Ultra-Shallow Junction Formation", Proceedings of the Eight International Workshop on: Fabrication, Characterization and Modeling Of Ultra-Shallow Doping Profiles in Semiconductors, June 2005, p. 327				
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	C5	P. A. Stolk et al., "Understanding and Controlling Transient Enhanced Dopant Diffusion in Silicon", Mat. Res. Soc. Symp. Proc. Vol. 354, pp. 307-318 (1995)				
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<b>Examiner Signature</b>	/Bernard Souw/				03/04/2009	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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